



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/614,553	07/07/2003	Edouard D. de Fresart	SCI1342ZP C01	5864
23125	7590	10/31/2005	EXAMINER	
FREESCALE SEMICONDUCTOR, INC. LAW DEPARTMENT 7700 WEST PARMER LANE MD:TX32/PL02 AUSTIN, TX 78729			DANG, TRUNG Q	
		ART UNIT	PAPER NUMBER	
			2823	

DATE MAILED: 10/31/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/614,553	DE FRESART ET AL. <i>(X2)</i>	
	Examiner	Art Unit	
	Trung Dang	2823	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on 11 August 2005.
- 2a) This action is FINAL. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) Claim(s) 34-64 and 70 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) Claim(s) 44,48-50,53,56,62 and 63 is/are allowed.
- 6) Claim(s) 34-43,45,51,55,57-61, and 70 is/are rejected.
- 7) Claim(s) 46,47,52 and 54 is/are objected to.
- 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) <input type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____.
3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.	5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)
	6) <input type="checkbox"/> Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 34-40, 42, 45, 51, 55, 57-61, 64, and 70 are rejected under 35 U.S.C. 103(a) as being unpatentable over Tung in view of Kitamura et al., all of record.

The rejection is maintained as of record and repeated herein.

With reference to the figure drawing 2F, Tung teaches a method of manufacturing a semiconductor component comprising the steps of:

providing a p-type substrate (200) having a surface;

forming by a LOCal Oxidation of Silicon (LOCOS) process a non-electrically conductive region (228) substantially located below a substantially planar plane defined by the surface of the substrate;

forming a drift region (250) in the substrate;

forming a channel region (221) in the substrate, at least a portion of the drift region (250) located between the channel region (221) and the non-electrically conductive region (228); and forming an electrically floating regions (219) in the substrate and contiguous with the non-electrically conductive region.

Note that p-type regions (219) are electrically floating regions because the regions 219 are not connected to any power source.

Tung differs from the claims in that while Tung forms the non-electrically conductive region (228) by LOCOS process, the claims call for a non-LOCOS process to form the same.

Kitamura et al. teach an advantage of a trench isolation over the conventional LOCOS isolation (Figs. 3A-3B and col. 6, lines 1-6; col. 9, lines 10-16; col. 10, lines 3-18).

It would have been obvious to one of ordinary skill in the art to modify Tung's process by forming the non-electrically conductive region (228) by a trench isolation process as suggested by Kitamura et al. because of the advantages mentioned in the above sections namely the withstand voltage is improved, the on-resistance and the cell pitch are reduced, thereby improving the performance of the device and increasing chip density per wafer.

For claim 34, the left most floating region 219 is located between the non-electrically conductive region 228 and the channel region 221 and it also located underneath region 228. Furthermore, the left most floating region 219 is also considered to be located **laterally** with respect to the non-electrically conductive region 228 because the term "lateral" is defined by the Random House College Dictionary Revised Edition as "of or pertaining to the side" or "directed to a side". Since claim 34 does not specify a particular side of the non-electrically conductive region at which the

floating region is located, the left most floating region 219 that is located at the bottom side of the non-electrically conductive region 228 (i.e., laterally with respect to region 228) reads on the newly added claimed limitation regarding the term "laterally".

Similarly, for the same reason noted above, the left most floating region 219 is considered to be located **laterally** between the non-electrically conductive region 228 (e.g. the right portion of region 228 shown in Fig. 2F) and the channel region 221 as claimed in claim 70.

For claim 35, see Figs. 2A and 2B for the formation of the channel region (221) and the electrically floating regions (219) occurs simultaneously with each other.

For claims 37-39, see col. 5, line14 and col. 8, lines 21-22 for the materials of the trench fillers.

As for claim 40, applicants do not challenge the Official notice made by the Examiner in the previous Office action.

For claim 42, Figs. 6 and 7 show planar trench surfaces, i.e., the trench fill materials are planarized.

For claim 51, the non-electrically conductive region 228 is located between the drain region 244 and the channel region 221; and the right most floating region 219 is located between region 228 and the drain region 244.

For claim 55, channel region (221) is electrically isolated from the substrate (202) located underneath the channel region because the channel region and the substrate have opposite type of conductivity.

For claim 57, the left most floating region 219 is located partially under the gate electrode 234.

3. Claim 41 is rejected under 35 U.S.C. 103(a) as being unpatentable over Tung taken with Kitamura as applied to claims 34-40, 42, 45, 51, 55, 57-61, 64 and 70 above, and further in view of Ishikawa of record.

The rejection is maintained as of record and repeated herein.

The combination of Tung and Kitamura et al. teaches a process as mentioned above. The combined process differs from the claims in not disclosing the claimed limitation of densifying the trench fill material. However, Ishikawa teaches that densifying an oxide filled in the trench would eliminate pits, which would have caused by subsequent planarizing process (col. 5, lines 14-19, lines 32-40). Thus, in the case where the trench is filled with an oxide as taught in Kitamura, it would have been obvious to one having ordinary skill in the art to densify the filled oxide as suggested by Ishikawa because this would eliminate pits hence improves reliability of the device.

4. Claims 43 is rejected under 35 U.S.C. 103(a) as being unpatentable over Tung taken with Kitamura et al. as applied to claims 34-40, 42, 45, 51, 55, 57-61, 64 and 70 above, and further in view of Yasuhara et al. of record.

The rejection is maintained as of record and repeated herein.

The combination of Tung and Kitamura et al. teaches a process as mentioned above. The combined process differs from the claims in not disclosing the claimed step of implanting a dose of oxygen into the surface of the substrate at location corresponding to the non-electrically conductive region. However, Yasuhara et al. in col. 5, lines 28-29 suggest that "The resistance of the film 14 can be adjusted by the concentration of oxygen contained therein..." Thus, one skilled in the art would recognize that incorporating oxygen into the SIPOS film would increase the resistance of the film because oxygen atoms would react with silicon atoms in the SIPOS to form silicon oxide that possesses insulation property. Therefore, in the case where the trench is filled with a semi-insulating polysilicon (SIPOS) as taught in Kitamura, it would have been obvious to one having ordinary skill in the art to incorporate oxygen into SIPOS film because this would increase the resistance of the SIPOS film, hence increasing the isolation property of the trench. Moreover, introducing oxygen atoms into a region by implantation is well known in the art. Thus, the limitation regarding implanting a dose of oxygen into the surface of the substrate at location corresponding to non-electrically conductive region (i.e., trench isolation region) is met.

Allowable Subject Matter

5. Claims 44 and its dependent claims 62 and 63 are allowed over prior art of record.

6. Claims 56 and its dependent claims 48, 49, 50, and 53 are allowed over prior art of record.
7. Claims 46, 47, 52, and 54 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
8. The following is a statement of reasons for the indication of allowable subject matter:

The above claims are allowed or indicated allowable over prior art of record because the prior art does not teach or suggest the claimed feature regarding the electrically floating region that is located at the surface of the substrate.

Response to Arguments

9. Applicant's arguments filed 8/11/05 have been fully considered but they are not persuasive.

With respect to claim 34, applicants argue that Figure 2F of Tung does not show portion of regions 219 are located lateral to region 228. The Examiner respectfully disagrees for the reason noted in the above rejection regarding the interpretation of the term "lateral".

For claim 51, applicants argue that the right most floating region 219 is not located between region 228 and region 244 of Tung. The Examiner respectfully disagrees. As shown in Fig. 2F, the right most region 219 is located between the drain region 244 and the left portion of region 228. Since the non-electrically conductive region of claim 51 is not necessarily limited to the entire region, the left portion of region 228 is readable on the claimed non-electrically conductive region.

Conclusion

10. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Trung Dang whose telephone number is 571-272-1857. The examiner can normally be reached on Mon-Friday 9:30am-6:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).


Trung Dang
Primary Examiner
Art Unit 2823

10/30/05